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0284163

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**INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT**

Applicant: INABA, Satoshi

Appln. No.: 10/042,264

Filing Date: January 11, 2002

Examiner: T. DICKEY

Group Art Unit: 2826

Date: July 29, 2003

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of

1

**U.S. PATENT DOCUMENTS**

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
Th	AR 5,583,361	12/1996	Morishita			
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Th	CR 4,819,043	04/1989	Yazawa et al.			
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	NR					

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**FOREIGN PATENT DOCUMENTS**

	Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
					Enclosed	No	Enclose	No
Th	OR 0 962 988 A2	12/1999	Europe	Higashi et al.	X		X	
Th	PR 60-50960	03/1985	Japan	Katsuhiro	X			X
Th	QR 7-335837	12/1995	Japan	Masabumi	X			X
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**OTHER (Including in this order: Author, Title, Periodical Name, Date, Pertinent Pages, etc.)**

Th	WR	MIYAMOTO et al., "Pseudo-SOI: P-N-P-Channel-Doped Bulk MOSFET for Low-Voltage High Performance Applications," Electron Devices Meeting, 1998, pages 15.3.1-15.3.4			
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	ZR				

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Date Consider d:

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

FORM PTO-1449 (modified)  
To: U.S. Department of Commerce  
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Date: September 15, 2003

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## FOREIGN PATENT DOCUMENTS

COMPLETION DOCUMENTS						English Abstract		Translation Readily Available		
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